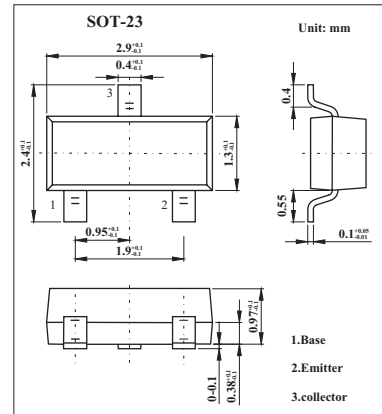


# FMMT493

■ Features

- Medium power transistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	120	V
Collector-emitter voltage	V <sub>CEO</sub>	100	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Peak collector current	I <sub>CM</sub>	2	A
Collector current	I <sub>C</sub>	1	A
Base current	I <sub>B</sub>	200	mA
Power dissipation	P <sub>tot</sub>	500	mW
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=100μA	120			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=10mA	100			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA	5			V
Collector cutoff current	ICBO	VCE=100V			100	nA
Emitter cut-off current	IEBO	VEB=4V			100	nA
Collector cutoff current	ICES	VCE=100V			100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=500mA, IB=50mA IC=1A, IB=100mA			0.3 0.6	V
Base-emitter saturation voltage *	VBE(sat)	IC=1A, IB=100mA			1.15	V
Base-emitter voltage *	VBE(ON)	IC=1A, VCE=10V			1.0	V
Static Forward Current Transfer Ratio	hFE	IC=1mA, VCE=10V*	100			
		IC=250mA, VCE=10V*	100		300	
		IC=500mA, VCE=10V*	60			
		IC=1A, VCE=10V*	20			
Transition Frequency	fT	IC=50mA, VCE=10V, f=100MHz	150			MHz
Collector-Base Breakdown Voltage	Cobo	VCE=10V, f=1MHz			10	pF

\* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	493
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